

	υ	1	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current *
1	Г:	С	L.	4 .5	us 20040036497	20040226	37	Semiconductor integrated circuit and its fabrication method	326/27	
2	r	r	r	r 1	US 20030215988	20031120	1 1	Self-aligned dual-gate transistor device and method of forming self-aligned dual-gate transistor device.	438/157	257/E21.
3	េ	r	r.	-	US 20030117151	20030626	45	Semiconductor device and method of checking semiconductor storage device	324/658	
4	г	r	۳	r		20021219	15	Semiconductor device and its manufacturing method	257/351	257/350; 257/369;
5	r.	п	r:	<b>-</b>	US 20020160574	20021031	21	METHOD OF FORMING A DUAL-GATED SEMICONDUCTOR-ON-INSULATOR DEVICE	438/283	257/E21.
6	г	r	г	r 1	US 20020086465	20020704	13	Sub-lithographics opening for back contact or back gate	438/149	257/347; 257/352;
7	Г	г	Г		US 20020070760	20020613	37	Semiconductor integrated circuit and its fabrication method	326/121	257/E27.
8	г	٣	۳	r i	US 20010009383	20010726	42	Semiconductor integrated circuit and its fabrication method	326/121	257/E27.
9	г	г	េ			20031021	36	Semiconductor integrated circuit and its fabrication method	326/102	257/E27.
10	Þ	г	r	٣	US 6359472	20020319	41	Semiconductor integrated circuit and its fabrication method	326/121	257/E27.i
11	R	г	n	Г	US 6194915	20010227		Semiconductor integrated circuit device and process for manufacturing the same	326/121	257/E27.
12	Þ	٣	۳	r	US 6049110	20000411		Body driven SOI-MOS field effect transistor	257/347	257/280; 257/281;
13	۱,	_		<u></u>	us 5523598	19960604	47	Semiconductor integrated circuit device	257/301	257/390; <u>*</u>

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